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Team Nexperia

74AHC02; 74AHCT02

Quad 2-input NOR gate Rev. 04 — 21 May 2008

Product data sheet

General description 1.

The 74AHC02; 74AHCT02 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC02; 74AHCT02 provides a quad 2-input NOR function.

Features 2.

- Balanced propagation delays
- All inputs have a Schmitt-trigger action
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - ◆ For 74AHC02: CMOS level
 - ◆ For 74AHCT02: TTL level
- ESD protection:
 - ◆ HBM EIA/JESD22-A114E exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
 - ◆ CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

Ordering information 3.

Table 1. **Ordering information**

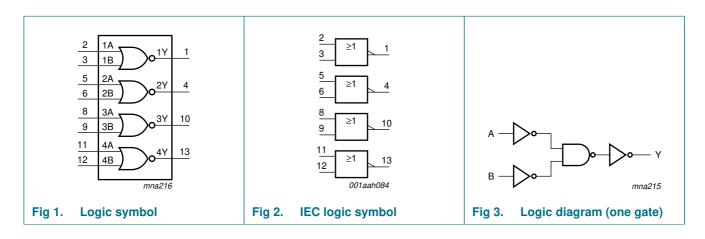
Type number	Package									
	Temperature range	Name	Description	Version						
74AHC02		'		'						
74AHC02D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1						
74AHC02PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1						
74AHC02BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5\times3\times0.85$ mm	SOT762-1						



 Table 1.
 Ordering information ...continued

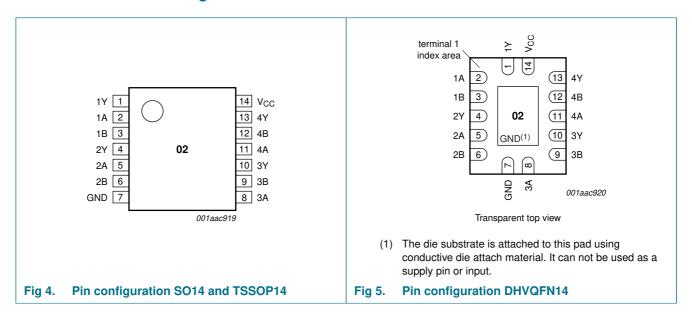
Type number	Package								
	Temperature range	Name	Description	Version					
74AHCT02									
74AHCT02D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1					
74AHCT02PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1					
74AHCT02BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5\times3\times0.85$ mm	SOT762-1					

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1Y	1	data output
1A	2	data input
1B	3	data input
2Y	4	data output
2A	5	data input
2B	6	data input
GND	7	ground (0 V)
3A	8	data input
3B	9	data input
3Y	10	data output
4A	11	data input
4B	12	data input
4Y	13	data output
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table [1]

Input	Output	
nA	nB	nY
L	L	Н
X	Н	L
Н	X	L

^[1] H = HIGH voltage level;

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		<i>y</i> , , , , , , , , , , , , , , , , , , ,		10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_1 < -0.5 \text{ V}$	<u>[1]</u> –20	-	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> –20	+20	mA
lo	output current	$V_O = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-25	+25	mA
I _{CC}	supply current		-	+75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHC0	2					
V _{CC}	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	100	ns/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V

L = LOW voltage level;

X = don't care.

^[2] For SO14 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K. For TSSOP14 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K. For DHVQFN14 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

 Table 5.
 Operating conditions ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHCT	02					
V _{CC}	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V _{CC} = 4.5 V to 5.5 V	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C 1	to +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC0	2									
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	٧
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	٧
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	٧
V _{IL}	LOW-level	$V_{CC} = 2.0 \text{ V}$	-	-	0.5	-	0.5	-	0.5	٧
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	٧
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	٧
V_{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_{O} = -50 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	1.9	-	٧
		$I_O = -50 \ \mu A; \ V_{CC} = 3.0 \ V$	2.9	3.0	-	2.9	-	2.9	-	٧
		$I_O = -50~\mu A;~V_{CC} = 4.5~V$	4.4	4.5	-	4.4	-	4.4	-	٧
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	٧
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	٧
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 50 \mu A$; $V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 50 \mu A$; $V_{CC} = 3.0 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 50 \mu A$; $V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	٧
		$I_O = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	٧
I	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
CC	supply current	V_{I} = V_{CC} or GND; I_{O} = 0 A; V_{CC} = 5.5 V	-	-	2.0	-	20	-	40	μΑ
Cı	input capacitance		-	3	10	-	10	-	10	pF

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C 1	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHCT	02		•		•	•				
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	8.0	-	8.0	-	0.8	V
V _{OH} HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$									
	output voltage	$I_O = -50 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
l _l	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	2.0	-	20	-	40	μΑ
$\Delta I_{ m CC}$	additional supply current	per input pin; $\begin{split} &V_I = V_{CC} - 2.1 \text{ V;} \\ &\text{other pins at } V_{CC} \text{ or GND;} \\ &I_O = 0 \text{ A; } V_{CC} = 4.5 \text{ V to } 5.5 \text{ V} \end{split}$	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance		-	3	10	-	10	-	10	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions		25 °C -		-40 °C to +85 °C		-40 °C to +125 °C		Unit	
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHC0	2										
t _{pd}	propagation	nA, nB to nY; see Figure 6	2]								
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		C _L = 15 pF		-	3.9	7.9	1.0	9.5	1.0	10.0	ns
		C _L = 50 pF		-	5.5	11.4	1.0	13	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C _L = 15 pF		-	2.9	5.5	1.0	6.5	1.0	7.0	ns
		$C_L = 50 pF$			4.2	7.5	1.0	8.5	1.0	9.5	ns
C_{PD}	power dissipation capacitance	C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[3]	-	7.0	-	-	-	-	-	pF

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions		25 °C		-40 °C 1	to +85 °C	-40 °C t	Unit		
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHCT02; V _{CC} = 4.5 V to 5.5 V											
t _{pd}	propagation	nA, nB to nY; see Figure 6	[2]								
	delay	C _L = 15 pF		-	3.8	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF		-	5.1	7.5	1.0	8.5	1.0	9.5	ns
C _{PD}	power dissipation capacitance	C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[3]	-	8.0	-	-	-	-	-	pF

- [1] Typical values are measured at nominal supply voltage ($V_{CC} = 3.3 \text{ V}$ and $V_{CC} = 5.0 \text{ V}$).
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

11. Waveforms

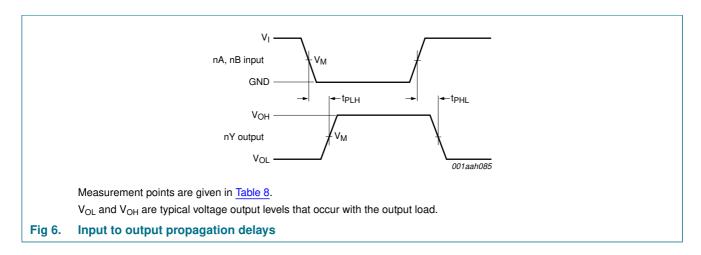
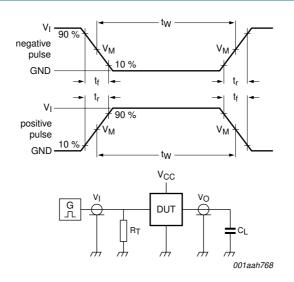


Table 8. Measurement points

Туре	Input	Output
	V _M	V _M
74AHC02	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT02	1.5 V	$0.5 \times V_{CC}$



Test data is given in Table 9.

Definitions test circuit:

 R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = load capacitance including jig and probe capacitance.

Fig 7. Load circuitry for measuring switching times

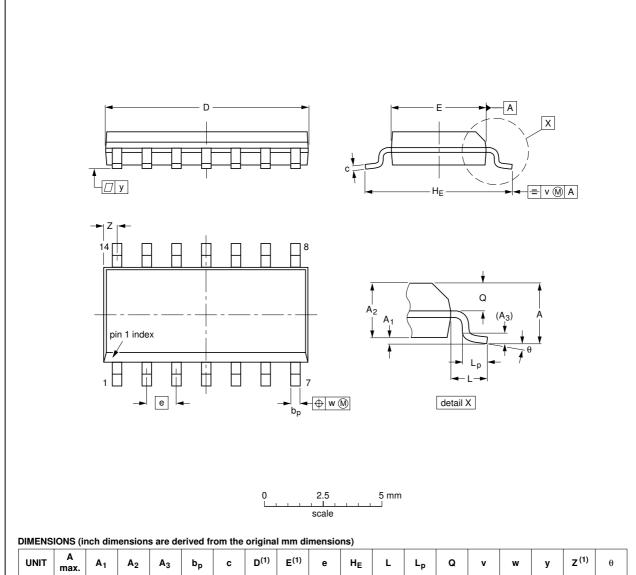
Table 9. Test data

Туре	Input		Load	Test
	VI	t _r , t _f	CL	
74AHC02	V _{CC}	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74AHCT02	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016		0.01	0.01	0.004	0.028 0.012	0°

Note

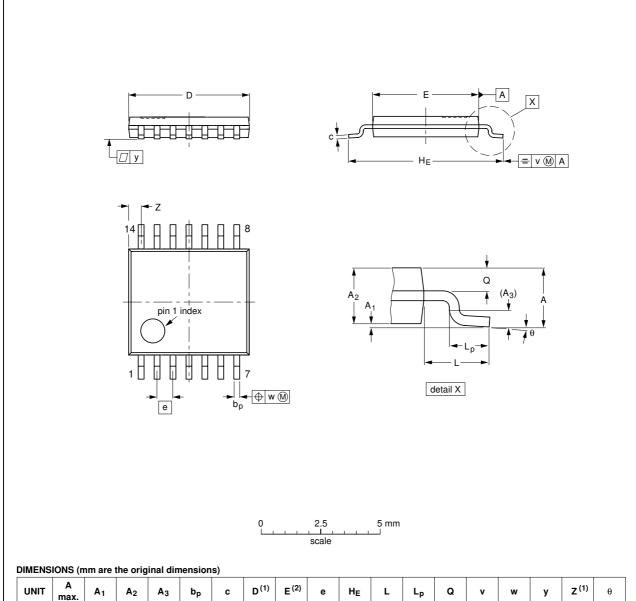
1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				99-12-27 03-02-19

Fig 8. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Ø	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT402-1		MO-153				99-12-27 03-02-18

Fig 9. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

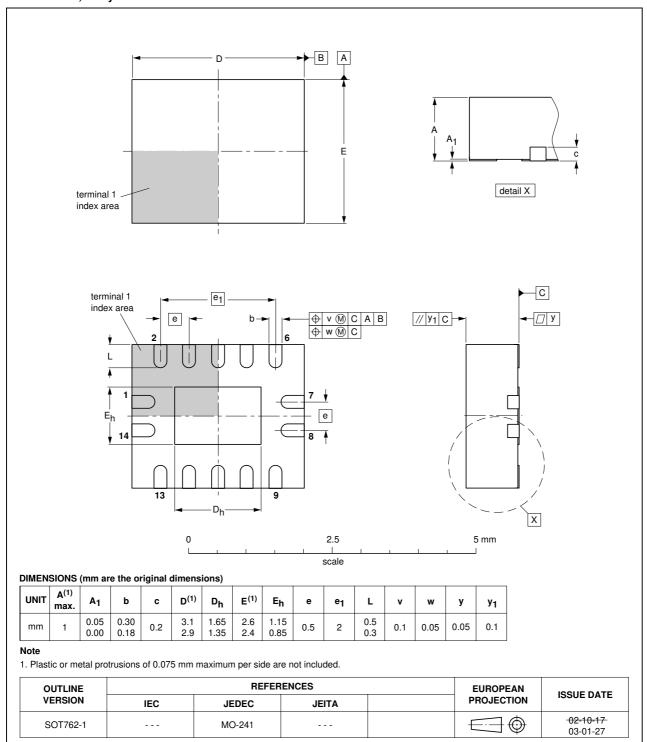


Fig 10. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74AHC_AHCT02_4	20080521	Product data sheet	-	74AHC_AHCT02_3		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guideline NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Table 6: the conditions for input leakage current have been changed. 					
74AHC_AHCT02_3	20080107	Product data sheet	-	74AHC_AHCT02_2		
74AHC_AHCT02_2	19990923	Product specification	-	74AHC_AHCT02_1		
74AHC_AHCT02_1	19981218	Product specification	-	-		

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

